



BC847BFAQ

45V NPN SMALL SIGNAL TRANSISTOR IN DFN0806

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

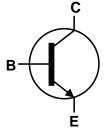
Features

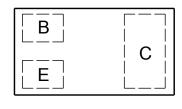
- $BV_{CEO} > 45V$
- I_C = 100mA High Collector Current
- P_D = 435mW Power Dissipation
- 0.48mm² Package Footprint, 16 Times Smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type BC857BFA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0008 grams (Approximate)







Device Symbol

Top View **Device Schematic**

Ordering Information (Notes 4 & 5)

Top View

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847BFAQ-7B	Automotive	1F	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

X2-DFN0806-3



Top View Bar Denotes Base and Emitter Side

1F = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	Ic	100	mA
Peak Pulse Collector Current	Ісм	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 6)	P_{D}	435	mW	
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	287	°C/W	
Thermal Resistance, Junction to Lead (Note 8)	$R_{ heta JL}$	150	°C/W	
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class	
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A	
Electrostatic Discharge – Machine Model	ESD MM	200	V	В	

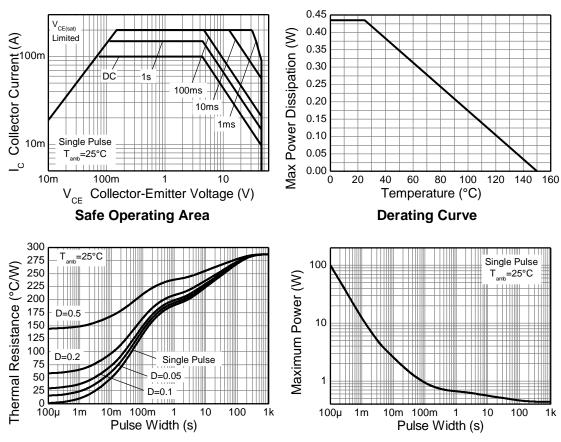
Notes:

- 6. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Transient Thermal Impedance

Pulse Power Dissipation



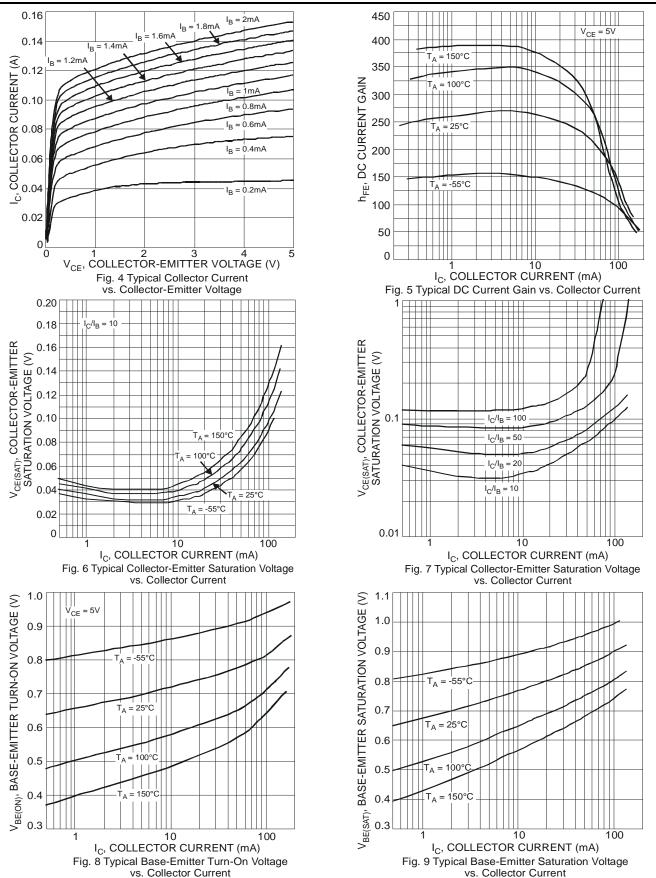
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	50	150	_	V	$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CES}	50	150	_		$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	45	65	_	V	$I_C = 1mA, I_B = 0$
Collector-Base Breakdown Voltage	BV _{EBO}	6.0	8.35	_	V	$I_E = 50\mu A, I_C = 0$
Collector-Base Cutoff Current	I _{CBO}	_	_	15	nA	$V_{CB} = 40V$
Collector-Emitter Cutoff Current	Ices	_	_	15	nA	V _{CE} = 40V
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h _{FE}	_	220	_	_	$I_C = 10\mu A, V_{CE} = 5.0V$
DC Current Gain		200	260 470	470		$I_C = 2.0 \text{mA}, V_{CE} = 5.0 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	50	125	mV	$I_C = 10mA, I_B = 0.5mA$
Collector-Emitter Saturation Voltage			122	300		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	760	1,000	mV	$I_C = 10mA, I_B = 0.5mA$
Dase-Emilier Saturation Voltage			880	1,100		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Voltage	V _{BE(ON)}	580	650	750	mV	$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$
Dase Emilier Voltage			725	800		$I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	Сово	_	1.5		pF	$V_{CB} = 10.0V$, $f = 1.0MHz$, $I_E = 0$
Current Gain-Bandwidth Product	f⊤	100	170		MHz	$V_{CE} = 5V, I_{C} = 10mA,$ f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

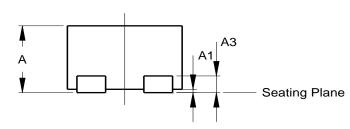


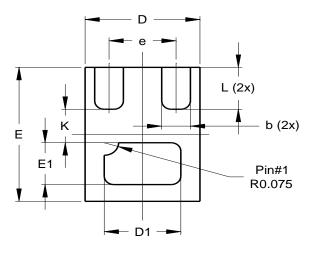


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0806-3



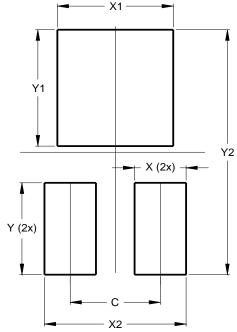


X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
А3	-	1	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	_	_	0.35		
K	_	_	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

X2-DFN0806-3



Dimensions	Value			
פווטופווסוטווס	(in mm)			
С	0.350			
X	0.200			
X1	0.450			
X2	0.550			
Υ	0.375			
Y1	0.475			
Y2	1.000			



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